SWITCHMODE Power Rectifiers

These state-of-the-art devices have the following features:

Features

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage Drop
- 175°C Operating Junction Temperature
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

Applications

- Ideally Suited for use as an Output Rectifier in High Frequency (up to 2 MHz) Automotive and Non-Automotive Applications
- Output Rectification in Compact Portable Consumer Applications
- Freewheeling Diode used with Inductive Loads

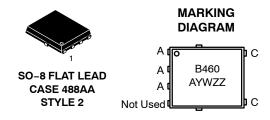


ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIERS 4 AMPERES 60 VOLTS





B460 = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
MBR460MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
MBR460MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NRVB460MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NRVB460MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_{R}	60	
Average Rectified Forward Current	I _{F(AV)}	4.0	Α
(Rated V_R , $T_C = 165^{\circ}C$)			
Peak Repetitive Forward Current,	I _{FRM}	8.0	Α
(Rated V_R , Square Wave, 20 kHz, $T_C = 165^{\circ}C$)			
Non-Repetitive Peak Surge Current	I _{FSM}	40	Α
(Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)			
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature	TJ	-55 to +175	°C
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E _{AS}	10	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Case, Steady State (Assumes 600 mm² 1 oz. copper bond pad, on a FR4 board)	$R_{ heta JC}$	-	2.4	°C/W
ELECTRICAL CHARACTERISTICS			•	•
Instantaneous Forward Voltage (Note 1) (i _F = 4 Amps, T _J = 125°C) (i _F = 4 Amps, T _J = 25°C)	VF	0.65 0.71	0.72 0.74	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T _J = 125°C) (Rated dc Voltage, T _J = 25°C)	i _R	6.5 0.01	20 0.2	mA

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

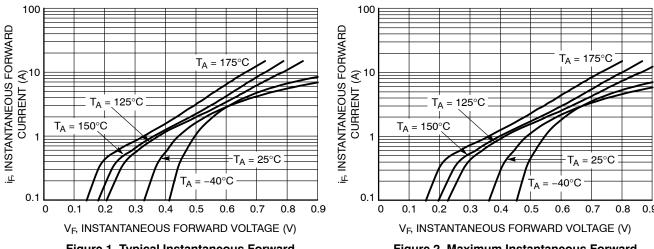


Figure 1. Typical Instantaneous Forward Characteristics

Figure 2. Maximum Instantaneous Forward Characteristics

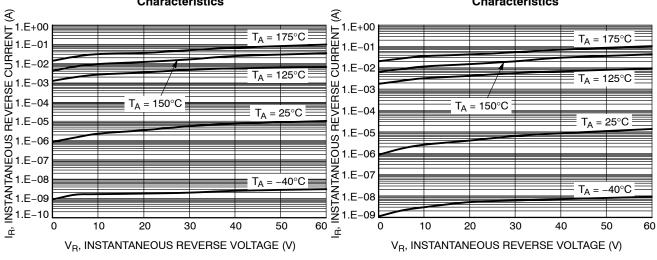


Figure 3. Typical Reverse Characteristics

Figure 4. Maximum Reverse Characteristics

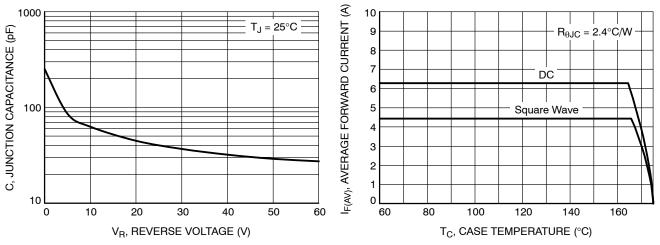


Figure 5. Typical Junction Capacitance

Figure 6. Current Derating TO-220AB

TYPICAL CHARACTERISTICS

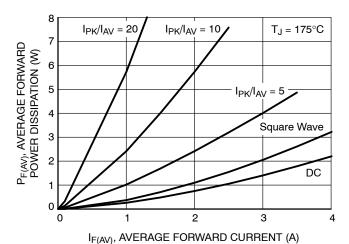


Figure 7. Forward Power Dissipation

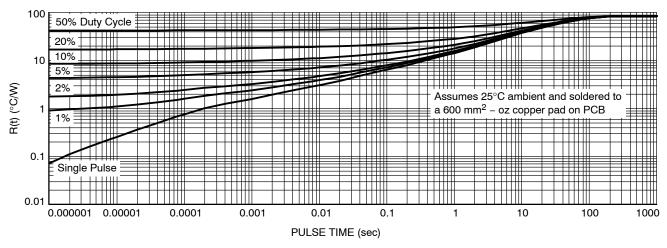


Figure 8. Thermal Characteristics





DFN5 5x6, 1.27P (SO-8FL) CASE 488AA ISSUE N

DATE 25 JUN 2018

NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION D1 AND E1 DO NOT INCLUDE
- MOLD FLASH PROTRUSIONS OR GATE BURRS

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.90	1.00	1.10
A1	0.00	-	0.05
b	0.33	0.41	0.51
С	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
е	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °		12 °

GENERIC MARKING DIAGRAM*

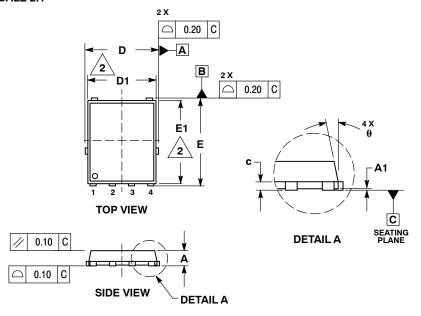


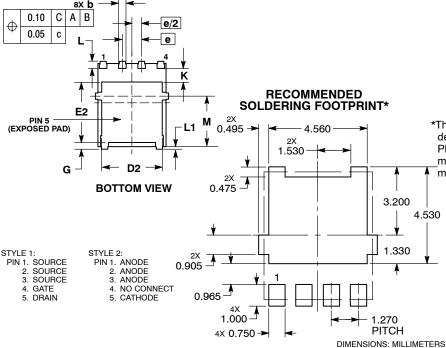
XXXXXX = Specific Device Code

= Assembly Location Α

Υ = Year W = Work Week = Lot Traceability ZZ

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.





*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)		PAGE 1 OF 1

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